

BLF6G20-45

UHF power LDMOS transistor

Rev. 01 — 20 February 2006

Objective data sheet

1. Product profile

1.1 General description

45 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

Table 1: Typical performance

RF performance at $T_{case} = 25\text{ }^{\circ}\text{C}$ in a common source class-AB production test circuit.

Mode of operation	f (MHz)	V_{DS} (V)	$P_{L(AV)}$ (W)	G_p (dB)	η_D (%)	ACPR (dBc)
2-carrier W-CDMA	1805 to 1880	28	2.5	17	14	-50 ^[1]

[1] Test signal: 3GPP; test model 1; 64 DPCH; PAR = 7.5 dB at 0.01 % probability on CCDF per carrier; carrier spacing 5 MHz

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

1.2 Features

- Typical 2-carrier W-CDMA performance at frequencies of 1805 MHz and 1880 MHz, a supply voltage of 28 V and an I_{DQ} of 350 mA:
 - ◆ Average output power = 2.5 W
 - ◆ Power gain = 17 dB (typ)
 - ◆ Efficiency = 14 %
 - ◆ ACPR = -50 dBc
- Easy power control
- Integrated ESD protection
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Internally matched for ease of use

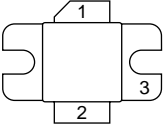
1.3 Applications

- RF power amplifiers for W-CDMA base stations and multi carrier applications in the 1800 MHz to 2000 MHz frequency range.

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2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	drain		<td>
2	gate		
3	source		

[1] Connected to flange

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
BLF6G20-45	-	flanged ceramic package; 2 mounting holes; 2 leads	SOT608A

4. Limiting values

Table 4: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
I_D	drain current		-	<td>	A
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	225	°C

5. Thermal characteristics

Table 5: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C};$ $P_L = <td>$	<td>	<td>	<td>	K/W

6. Characteristics

Table 6: Characteristics

$T_j = 25^\circ\text{C}$ per section; unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.5\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 60\text{ mA}$	<tbid>	1.6	<tbid>	V
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28\text{ V}; I_D = 300\text{ mA}$	<tbid>	2	<tbid>	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	1.5	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; V_{DS} = 10\text{ V}$	9	11	-	A
I_{GSS}	gate leakage current	$V_{GS} = 13\text{ V}; V_{DS} = 0\text{ V}$	-	-	150	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 3\text{ A}$	-	<tbid>	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V}; I_D = 2.1\text{ A}$	-	0.25	<tbid>	Ω
C_{rs}	feedback capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}; f = 1\text{ MHz}$	-	<tbid>	-	pF

7. Application information

Table 7: Application information

Mode of operation: 2-carrier W-CDMA; PAR 7.5 dB at 0.01 % probability on CCDF; 3GPP test model 1; 1-64 PDPCH; $f_1 = 1807.5\text{ MHz}; f_2 = 1812.5\text{ MHz}; f_3 = 1872.5\text{ MHz}; f_4 = 1877.5\text{ MHz}$; RF performance at $V_{DS} = 28\text{ V}; I_{Dq} = 2 \times 900\text{ mA}; T_{case} = 25^\circ\text{C}$; unless otherwise specified; in a class-AB production test circuit

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{L(AV)}$	average output power		-	2.5	-	W
G_p	power gain	$P_{L(AV)} = 2.5\text{ W}$	<tbid>	17	-	dB
η_D	drain efficiency	$P_{L(AV)} = 2.5\text{ W}$	<tbid>	14	-	%
IMD3	third order intermodulation distortion	$P_{L(AV)} = 2.5\text{ W}$	-	<tbid>	<tbid>	dBc
ACPR	adjacent channel power ratio	$P_{L(AV)} = 2.5\text{ W}$	-	-50	<tbid>	dBc

7.1 Ruggedness in class-AB operation

The BLF6G20-45 is capable of withstanding a load mismatch corresponding to $V_{SWR} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 28\text{ V}; I_{Dq} = 350\text{ mA}; P_L = 45\text{ W (CW)}; f = 1880\text{ MHz}$.

8. Package outline

Flanged ceramic package; 2 mounting holes; 2 leads

SOT608A

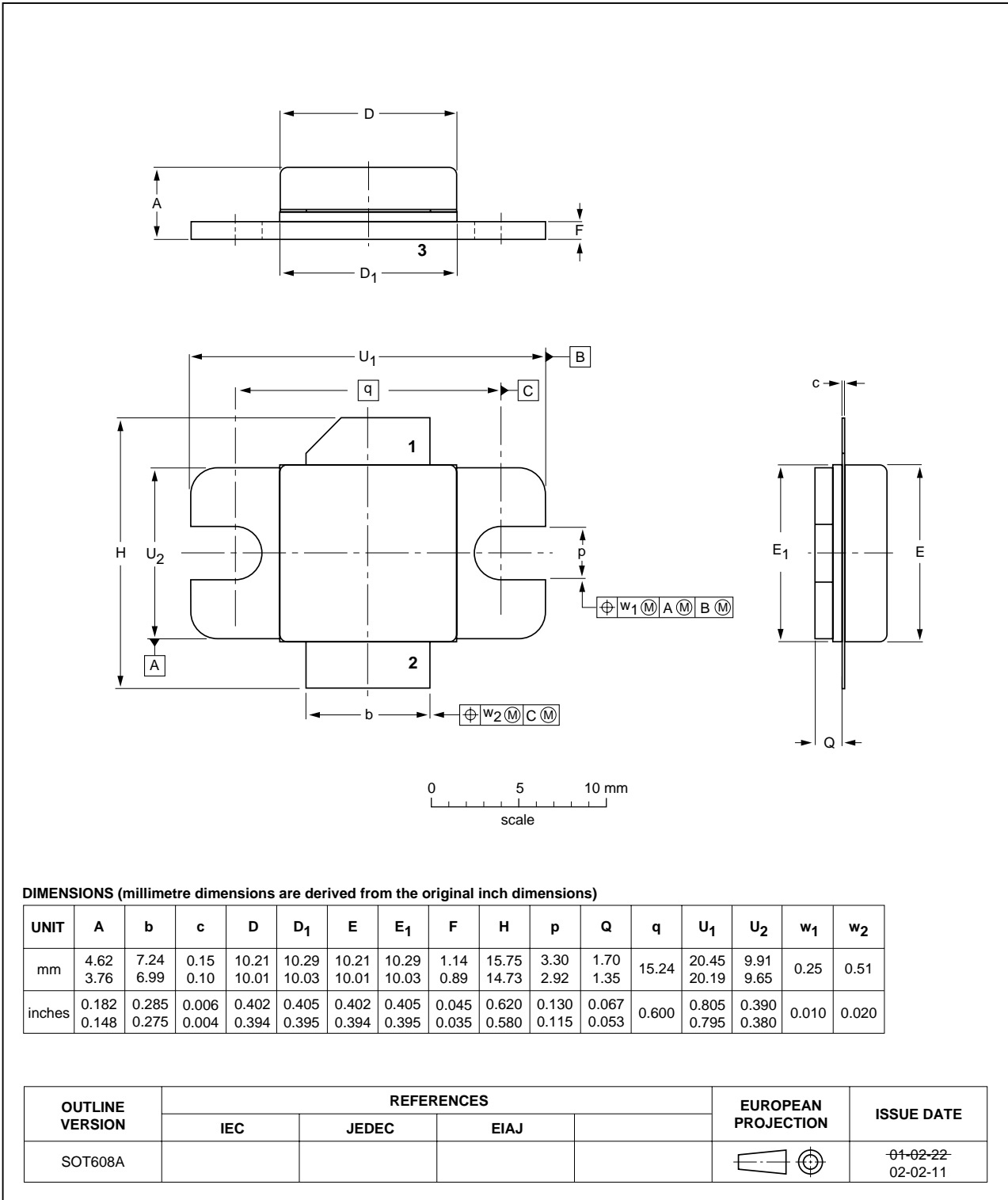


Fig 1. Package outline SOT608A

9. Abbreviations

Table 8: Abbreviations

Acronym	Description
3GPP	Third Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average power Ratio
PDPCH	transmission Power of the Dedicated Physical CHannel
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access



10. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BLF6G20-45_1	20060220	Objective data sheet	-	-	-

11. Data sheet status

Level	Data sheet status ^[1]	Product status ^[2] ^[3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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